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respect to a first axis oriented perpendicular to said new sputter surface, a substrate carrier which is arranged to be drivingly rotatable about a second axis, wherein said first and said second axes are oblique with respect to one another at an angle of less than 90°, and said sputtering source is a magnetron sputtering source with at least one closed loop, tunnel-shaped magnetic field pattern around said first axis with constant field polarity as viewed in a direction along said closed loop.

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C/2
47. (Amended) The chamber of claim 35, wherein said new sputter surface is substantially rotationally symmetrical with respect to said first axis and has a diameter Φ_T and wherein a locus of smallest mutual spacing of said first and of said second axes has a distance D to said new sputter surface and wherein $3/4 \leq \Phi_T / D \leq 2$.

48. (Amended) The chamber of claim 47, wherein Φ_T equals approximately 1.2 D.

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C/2
50. (Amended) The chamber of claim 49, further comprising at least one of said substrate on said receiving surface, said locus being situated at least approximately on a plane defined by a surface of said at least one substrate to be sputter coated.